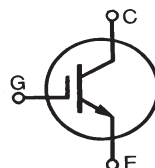


High Voltage IGBTs

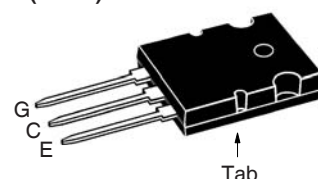
IXGK100N170 IXGX100N170

$$\begin{aligned} V_{CES} &= 1700V \\ I_{C90} &= 100A \\ V_{CE(sat)} &\leq 3.0V \end{aligned}$$

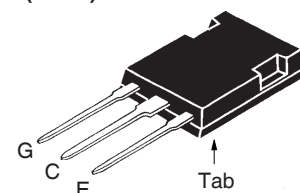


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	170	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C90}	$T_C = 90^\circ\text{C}$	100	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	600	A
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ $@ 0.8 \cdot V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V, V_{CE} = 1250V, T_J = 125^\circ\text{C}$ $R_G = 10\Omega, \text{Non Repetitive}$	10	μs
P_C	$T_C = 25^\circ\text{C}$	830	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247 (IXGX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction and Switching Losses
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

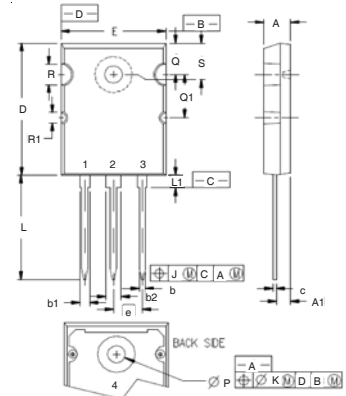
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 3\text{mA}, V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 8\text{mA}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 100A, V_{GE} = 15V, \text{Note 1}$		2.5	3.0 V

Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values

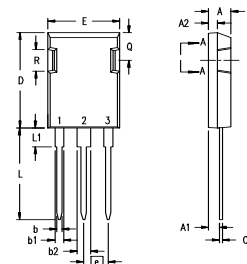
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	36	64	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9200	pF
C_{oes}			455	pF
C_{res}			150	pF
Q_g	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		425	nC
Q_{ge}			65	nC
Q_{gc}			186	nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
t_r			192	ns
$t_{d(off)}$			285	ns
t_f			395	ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
t_r			250	ns
$t_{d(off)}$			285	ns
t_f			435	ns
R_{thJC}			0.15	$^\circ\text{C/W}$
R_{thCS}				$^\circ\text{C/W}$

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-264 Outline


Terminals: 1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ Outline


Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

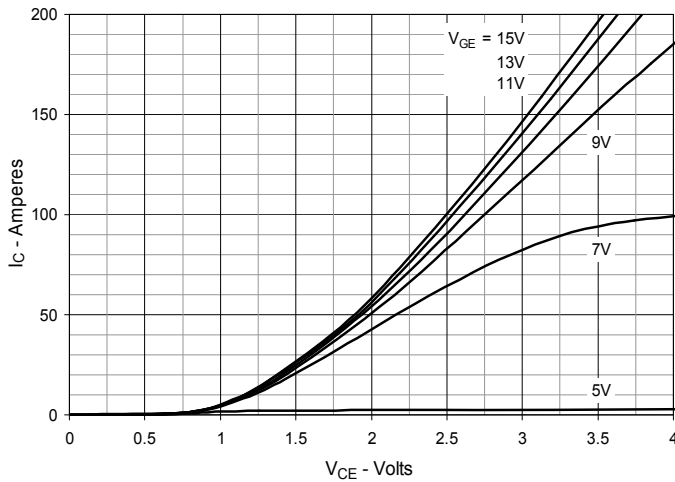


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

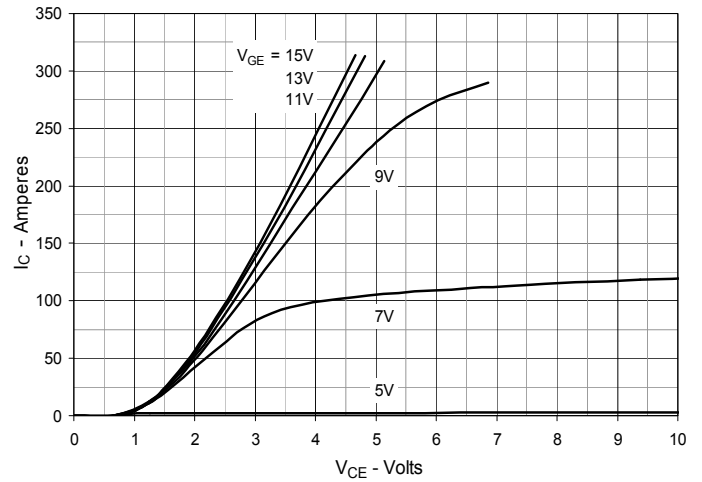


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

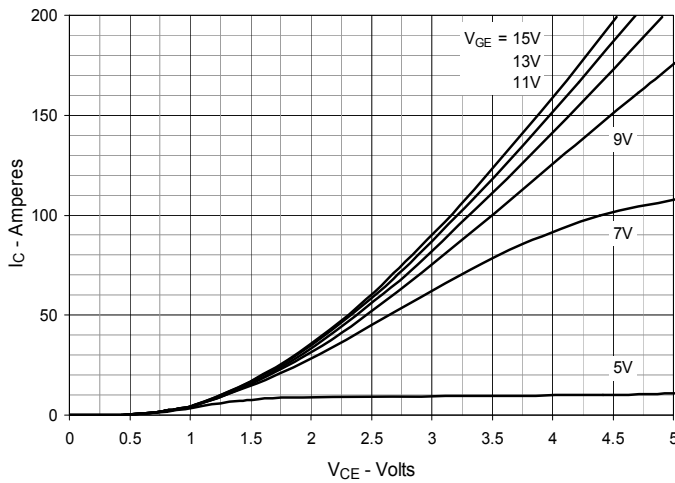


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

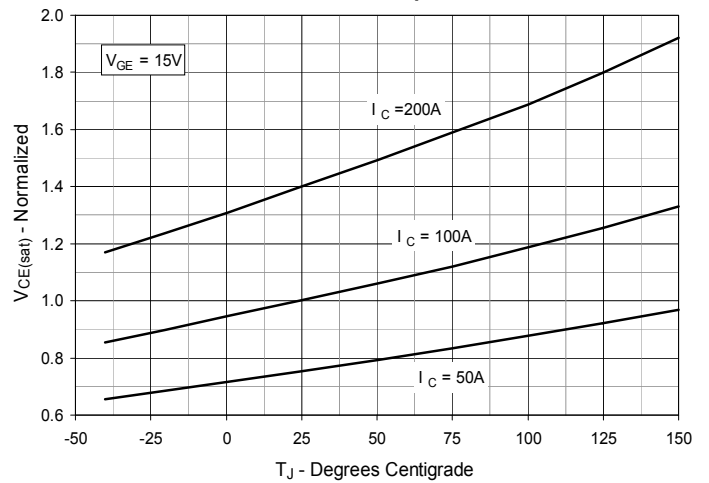


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

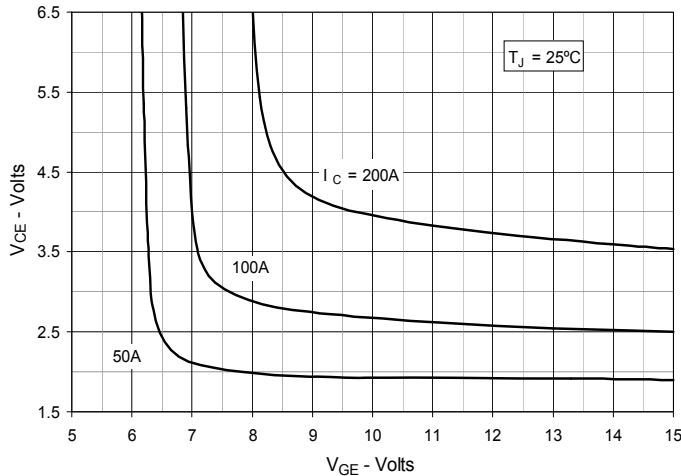


Fig. 6. Input Admittance

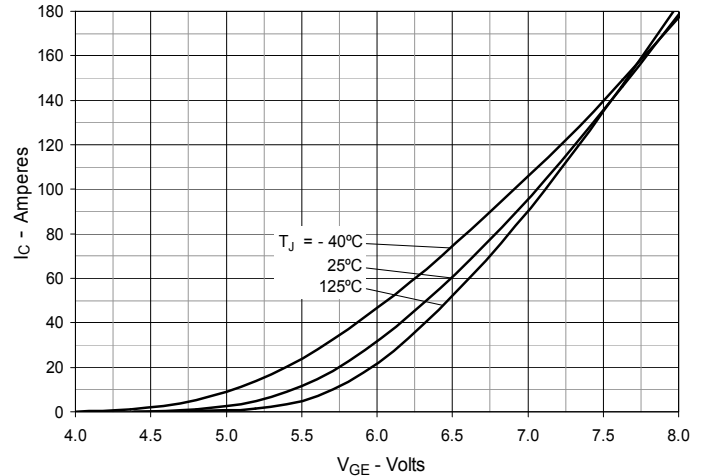


Fig. 7. Transconductance

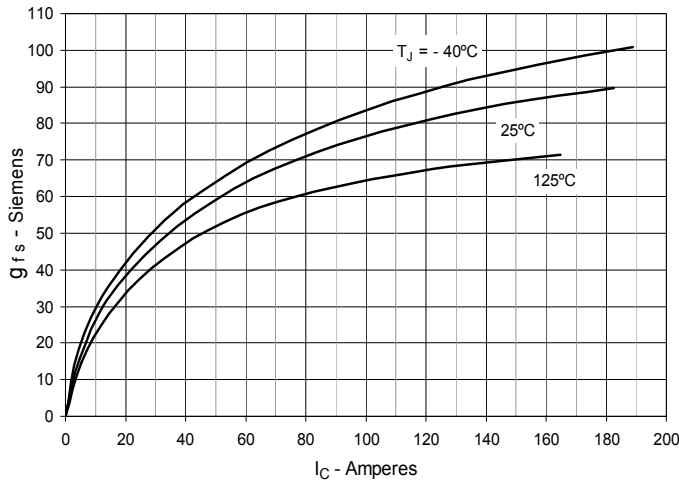


Fig. 8. Gate Charge

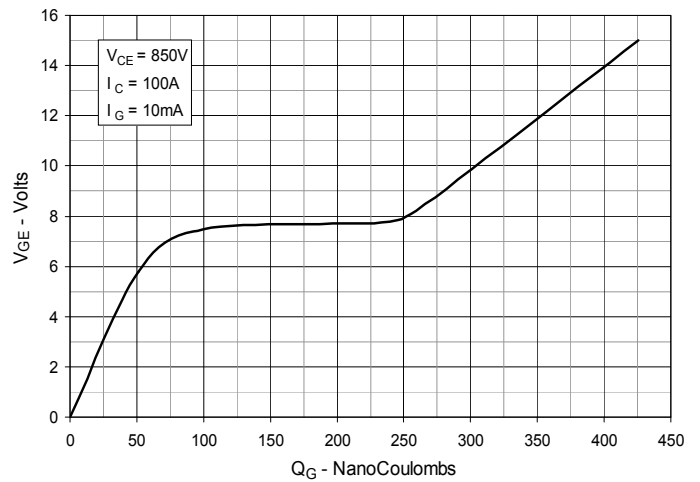


Fig. 9. Reverse-Bias Safe Operating Area

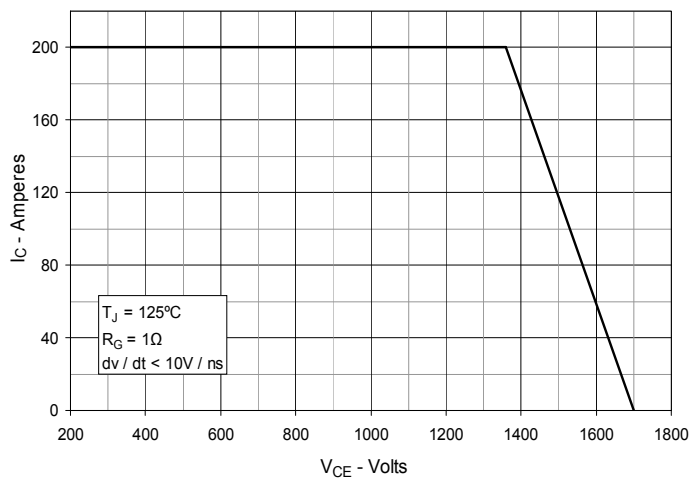


Fig. 10. Capacitance

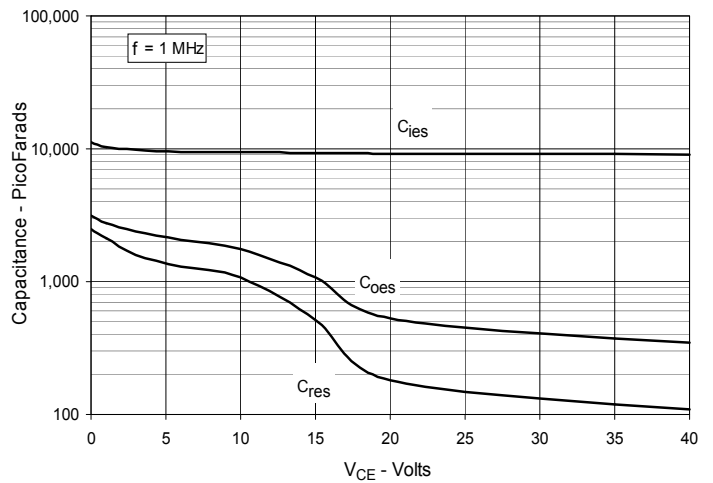


Fig. 11. Maximum Transient Thermal Impedance

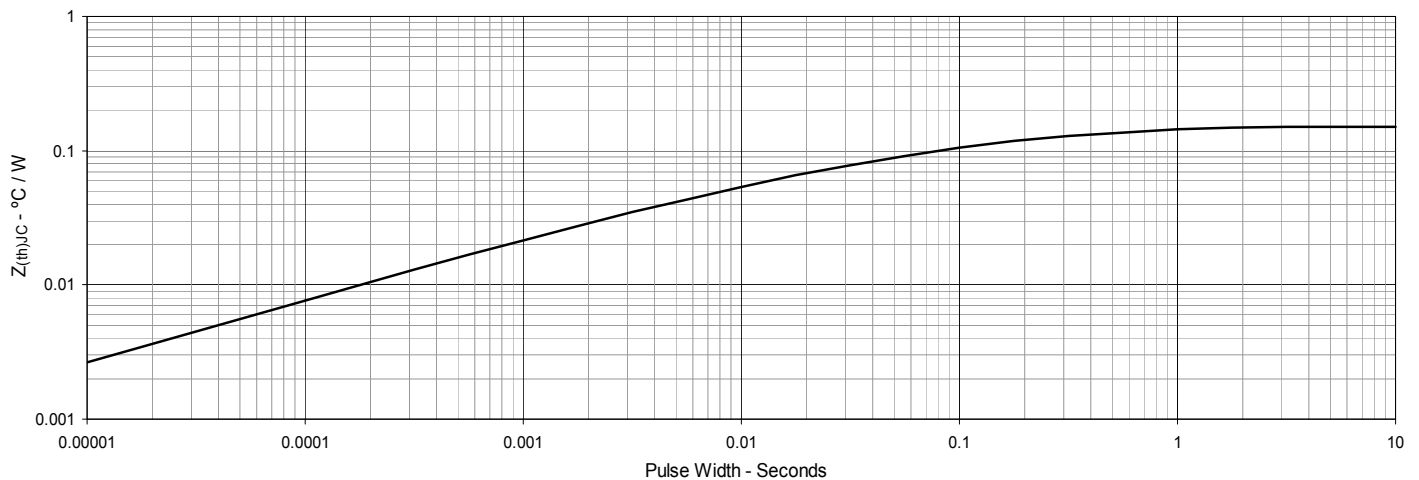
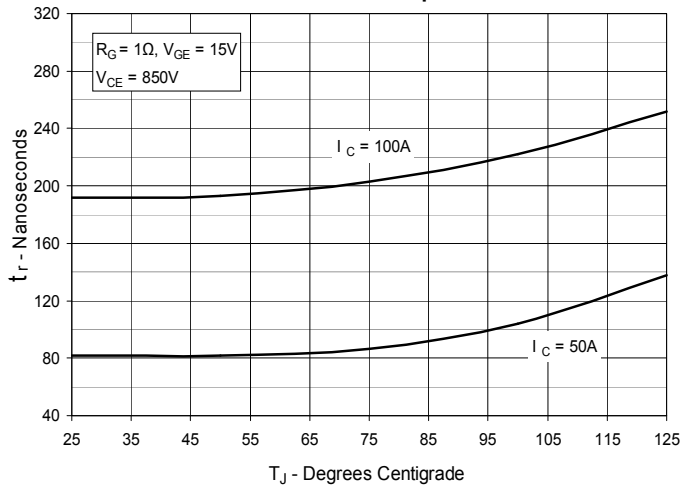
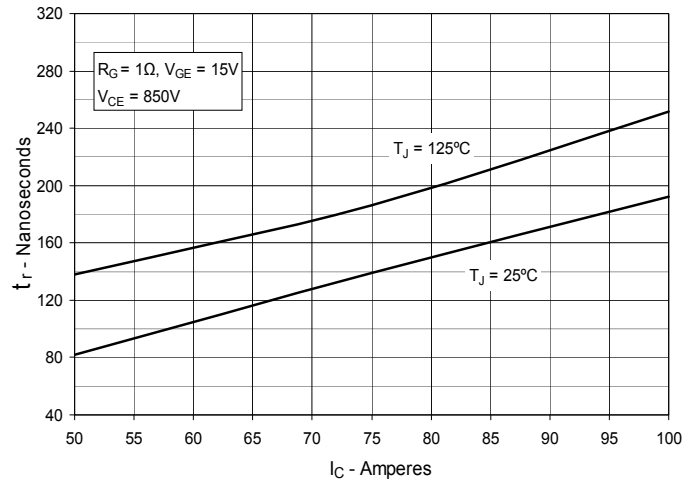
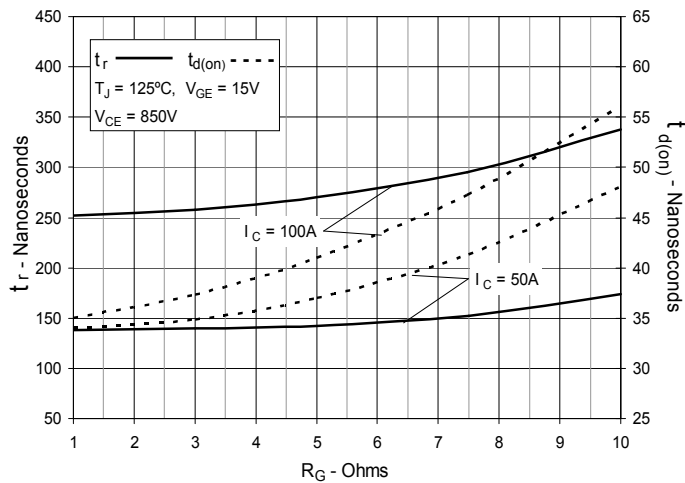
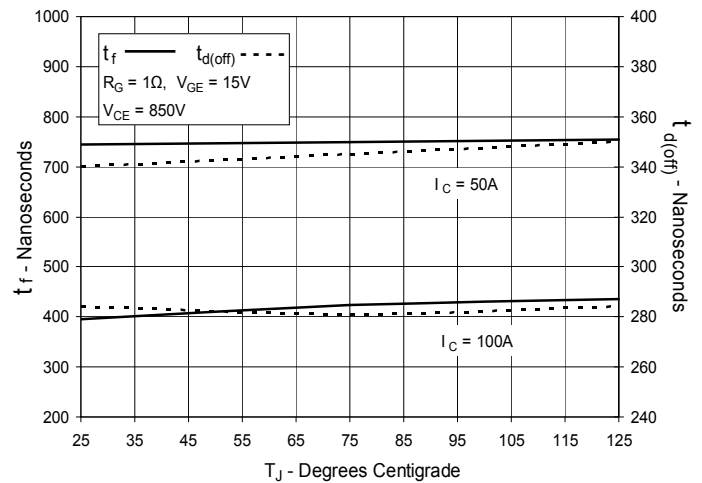
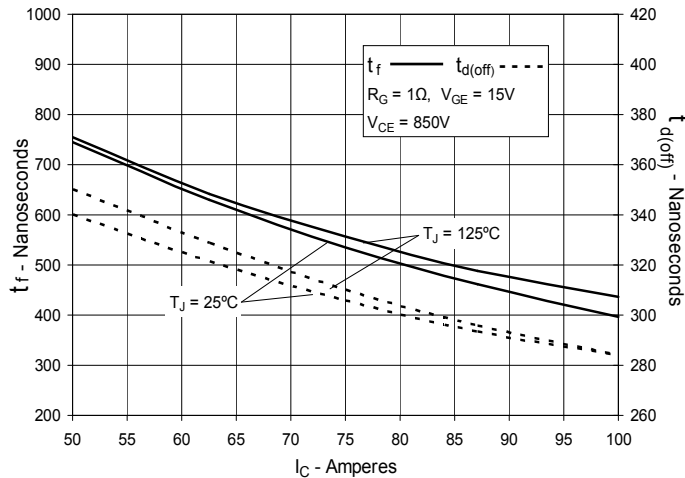
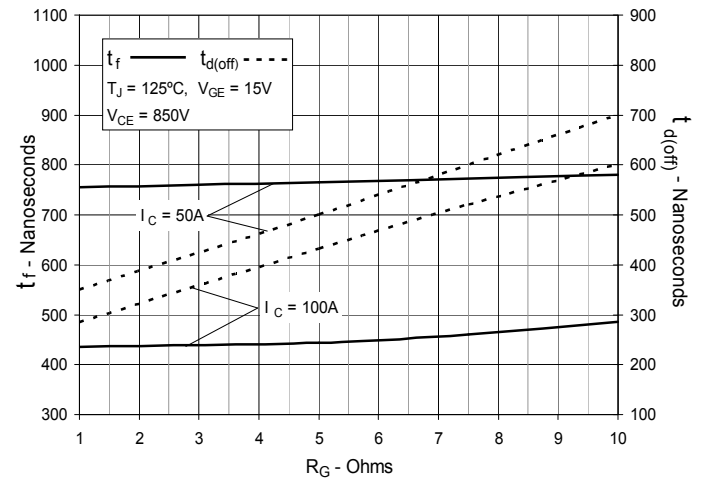


Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance




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